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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	157
Number of Gates	250000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p250l-fg256i

Email: info@E-XFL.COM

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Flash*Freeze Technology and Low Power Modes

Flash*Freeze Mode

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 FPGAs offer an ultra-low static power mode to reduce power consumption while preserving the state of the registers, SRAM contents, and I/O states (IGLOO nano and IGLOO PLUS only) without switching off any power supplies, inputs, or input clocks.

Flash*Freeze technology enables the user to switch to Flash*Freeze mode within 1 µs, thus simplifying low power design implementation. The Flash*Freeze (FF) pin (active Low) is a dedicated pin used to enter or exit Flash*Freeze mode directly; or the pin can be routed internally to the FPGA core and state management IP to allow the user's application to decide if and when it is safe to transition to this mode. If the FF pin is not used, it can be used as a regular I/O.

The FF pin has a built-in glitch filter and optional Schmitt trigger (not available for all devices) to prevent entering or exiting Flash*Freeze mode accidentally.

There are two ways to use Flash*Freeze mode. In Flash*Freeze type 1, entering and exiting the mode is exclusively controlled by the assertion and deassertion of the FF pin. This enables an external processor or human interface device to directly control Flash*Freeze mode; however, valid data must be preserved using standard procedures (refer to the "Flash*Freeze Mode Device Behavior" section on page 30). In Flash*Freeze mode type 2, entering and exiting the mode is controlled by both the FF pin AND user-defined logic. Flash*Freeze management IP may be used in type 2 mode for clock and data management while entering and exiting Flash*Freeze mode.

Flash*Freeze Type 1: Control by Dedicated Flash*Freeze Pin

Flash*Freeze type 1 is intended for systems where either the device will be reset upon exiting Flash*Freeze mode, or data and clock are managed externally. The device enters Flash*Freeze mode 1 µs after the dedicated FF pin is asserted (active Low), and returns to normal operation when the FF pin is deasserted (High) (Figure 2-1 on page 25). In this mode, FF pin assertion or deassertion is the only condition that determines entering or exiting Flash*Freeze mode.

In Libero[®] System-on-Chip (SoC) software v8.2 and before, this mode is implemented by enabling Flash*Freeze mode (default setting) in the Compile options of the Microsemi Designer software. To simplify usage of Flash*Freeze mode, beginning with Libero software v8.3, an INBUF_FF I/O macro was introduced. An INBUF_FF I/O buffer must be used to identify the Flash*Freeze input. Microsemi recommends switching to the new implementation.

In Libero software v8.3 and later, the user must manually instantiate the INBUF_FF macro in the top level of the design to implement Flash*Freeze Type 1, as shown in Figure 2-1 on page 25.

Flash*Freeze Technology and Low Power Modes

Table 2-4 summarizes the Flash*Freeze mode implementations.

Flash*Freeze Mode Type	Description	Flash*Freeze Pin State	Instantiate ULSICC Macro	LSICC Signal	Operating Mode
	Flash*Freeze mode is		No	N/A	Normal operation
	controlled only by the FF pin.	Asserted	No	N/A	Flash*Freeze mode
2	Flash*Freeze mode is controlled by the FF pin and LSICC signal.		Yes	Deasserted	Normal operation
		Deasserted	Yes	"Don't care"	Normal operation
		Asserted	Yes	Asserted	Flash*Freeze mode

Table 2-4 •	Flash*Freeze	Mode Usage
-------------	--------------	------------

Note: Refer to Table 2-3 on page 26 for Flash*Freeze pin and LSICC signal assertion and deassertion values.

IGLOO, ProASIC3L, and RT ProASIC3 I/O State in Flash*Freeze Mode

In IGLOO and ProASIC3L devices, when the device enters Flash*Freeze mode, I/Os become tristated. If the weak pull-up or pull-down feature is used, the I/Os will maintain the configured weak pull-up or pull-down status. This feature enables the design to set the I/O state to a certain level that is determined by the pull-up/-down configuration.

Table 2-5 shows the I/O pad state based on the configuration and buffer type.

Note that configuring weak pull-up or pull-down for the FF pin is not allowed. The FF pin can be configured as a Schmitt trigger input in IGLOOe, IGLOO nano, IGLOO PLUS, and ProASIC3EL devices.

Table 2-5 • IGLOO, ProASIC3L, and RT ProASIC3 Flash*Freeze Mode (type 1 and type 2)—I/O Pad State

Buffer Type		I/O Pad Weak Pull-Up/-Down	I/O Pad State in Flash*Freeze Mode
Input/Global		Enabled	Weak pull-up/pull-down*
		Disabled	Tristate*
Output		Enabled	Weak pull-up/pull-down
		Disabled	Tristate
Bidirectional / Tristate E = 0		Enabled	Weak pull-up/pull-down*
Buffer	(input/tristate)	Disabled	Tristate*
	E = 1 (output)	Enabled	Weak pull-up/pull-down
		Disabled	Tristate

* Internal core logic driven by this input/global buffer will be tied High as long as the device is in Flash*Freeze mode.

Flash*Freeze Technology and Low Power Modes

- The INBUF_FF must be driven by a top-level input port of the design.
- The INBUF_FF AND the ULSICC macro must be used to enable type 2 Flash*Freeze mode.
- · For type 2 Flash*Freeze mode, the INBUF_FF MUST drive some logic in the design.
- For type 1 Flash*Freeze mode, the INBUF_FF may drive some logic in the design, but it may also be left floating.
- Only one INBUF_FF may be instantiated in a device.
- The FF pin threshold voltages are defined by VCCI and the supported single-ended I/O standard in the corresponding I/O bank.
- The FF pin Schmitt trigger option may be configured in the I/O attribute editor in Microsemi's Designer software. The Schmitt trigger option is only available for IGLOOe, IGLOO nano, IGLOO PLUS, ProASIC3EL, and RT ProASIC3 devices.
- A 2 ns glitch filter resides in the Flash*Freeze Technology block to filter unwanted glitches on the FF pin.

ULSICC

The User Low Static ICC (ULSICC) macro allows the FPGA core to access the Flash*Freeze Technology block so that entering and exiting Flash*Freeze mode can be controlled by the user's design. The ULSICC macro enables a hard block with an available LSICC input port, as shown in Figure 2-3 on page 27 and Figure 2-10 on page 37. Design rules for the ULSICC macro are as follows:

- The ULSICC macro by itself cannot enable Flash*Freeze mode. The INBUF_FF AND the ULSICC macro must both be used to enable type 2 Flash*Freeze mode.
- The ULSICC controls entering the Flash*Freeze mode by asserting the LSICC input (logic '1') of the ULSICC macro. The FF pin must also be asserted (logic '0') to enter Flash*Freeze mode.
- When the LSICC signal is '0', the device cannot enter Flash*Freeze mode; and if already in Flash*Freeze mode, it will exit.
- When the ULSICC macro is not instantiated in the user's design, the LSICC port will be tied High.

Flash*Freeze Management IP

The Flash*Freeze management IP can be configured with the Libero (or SmartGen) core generator in a simple, intuitive interface. With the core configuration tool, users can select the number of clocks to be gated, and select whether or not to implement housekeeping. All port names on the Flash*Freeze management IP block can be renamed by the user.

- The clock gating (filter) blocks include CLKINT buffers for each gated clock output (version 8.3).
- When housekeeping is NOT used, the WAIT_HOUSEKEEPING signal will be automatically fed back into DONE_HOUSEKEEPING inside the core, and the ports will not be available at the IP core interface.
- The INBUF_FF macro is automatically instantiated within the IP core.
- The INBUF_FF port (default name is "Flash_Freeze_N") must be connected to a top-level input port of the design.
- The ULSICC macro is automatically instantiated within the IP core, and the LSICC signal is driven by the FSM.
- Timing analysis can be performed on the clock domain of the source clock (i.e., input to the clock gating filters). For example, if CLKin becomes CLKin_gated, the timing can be performed on the CLKin domain in SmartTime.
- The gated clocks can be added to the clock list if the user wishes to analyze these clocks specifically. The user can locate the gated clocks by looking for instance names such as those below:

```
Top/ff1/ff_1_wrapper_inst/user_ff_1_wrapper/Primary_Filter_Instance/
Latch_For_Clock_Gating:Q
Top/ff1/ff_1_wrapper_inst/user_ff_1_wrapper/genblk1.genblk2.secondary_filter[0].
seconday_filter_instance/Latch_For_Clock_Gating:Q
Top/ff1/ff_1_wrapper_inst/user_ff_1_wrapper/genblk1.genblk2.secondary_filter[1].
seconday_filter_instance/Latch_For_Clock_Gating:Q
```

External I/O Clock Source

External I/O refers to regular I/O pins. The clock source is instantiated with one of the various INBUF options and accesses the CCCs via internal routing. The user has the option of assigning this input to any of the I/Os labeled with the I/O convention *IOuxwByVz*. Refer to the "User I/O Naming Conventions in I/O Structures" chapter of the appropriate device user's guide, and for Fusion, refer to the *Fusion Family of Mixed Signal FPGAs* datasheet for more information. Figure 4-11 gives a brief explanation of external I/O usage. Choosing this option provides the freedom of selecting any user I/O location but introduces additional delay because the signal connects to the routed clock input through internal routing before connecting to the CCC reference clock input.

For the External I/O option, the routed signal would be instantiated with a PLLINT macro before connecting to the CCC reference clock input. This instantiation is conveniently done automatically by SmartGen when this option is selected. Microsemi recommends using the SmartGen tool to generate the CCC macro. The instantiation of the PLLINT macro results in the use of the routed clock input of the I/O to connect to the PLL clock input. If not using SmartGen, manually instantiate a PLLINT macro before the PLL reference clock to indicate that the regular I/O driving the PLL reference clock should be used (see Figure 4-11 for an example illustration of the connections, shown in red).

In the above two options, the clock source must be instantiated with one of the various INBUF macros. The reference clock pins of the CCC functional block core macros must be driven by regular input macros (INBUFs), not clock input macros.



Figure 4-11 • Illustration of External I/O Usage

For Fusion devices, the input reference clock can also be from the embedded RC oscillator and crystal oscillator. In this case, the CCC configuration is the same as the hardwired I/O clock source, and users are required to instantiate the RC oscillator or crystal oscillator macro and connect its output to the input reference clock of the CCC block.

Figure 4-36 • Second-Stage PLL Showing Input of 256 MHz from First Stage and Final Output of 280 MHz

Figure 4-37 shows the simulation results, where the first PLL's output period is 3.9 ns (~256 MHz), and the stage 2 (final) output period is 3.56 ns (~280 MHz).

Stage 2 Output Clock Period Stage 1 Output Clock Period

Figure 4-37 • Model Sim Simulation Results

Conclusion

The advanced CCCs of the IGLOO and ProASIC3 devices are ideal for applications requiring precise clock management. They integrate easily with the internal low-skew clock networks and provide flexible frequency synthesis, clock deskewing, and/or time-shifting operations.

Related Documents

Application Notes

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

Datasheets

Fusion Family of Mixed Signal FPGAs http://www.microsemi.com/soc/documents/Fusion_DS.pdf

User's Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3 libguide ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The "Implementing EXTFB in ProASIC3/E Devices" section is new (SAR 36647).	86
	Table 4-7 • Delay Values in Libero SoC Software per Device Family was added to the "Clock Delay Adjustment" section (SAR 22709).	102
	The "Phase Adjustment" section was rewritten to explain better why the visual CCC shows both the actual phase and the actual delay that is equivalent to this phase shift (SAR 29647).	103
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663)	128, 129
December 2011	Figure 4-20 • PLL Block Diagram, Figure 4-22 • CCC Block Control Bits – Graphical Representation of Assignments, and Table 4-12 • MUXA, MUXB, MUXC were revised to change the phase shift assignments for PLLs 4 through 7 (SAR 33791).	101, 105, 109
June 2011	The description for RESETEN in Table 4-8 • Configuration Bit Descriptions for the CCC Blocks was revised. The phrase "and should not be modified via dynamic configuration" was deleted because RESETEN is read only (SAR 25949).	106
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A

Conclusion

Fusion, IGLOO, and ProASIC3 devices provide users with extremely flexible SRAM blocks for most design needs, with the ability to choose between an easy-to-use dual-port memory or a wide-word two-port memory. Used with the built-in FIFO controllers, these memory blocks also serve as highly efficient FIFOs that do not consume user gates when implemented. The SmartGen core generator provides a fast and easy way to configure these memory elements for use in designs.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes				
August 2012	The note connected with Figure 6-3 • Supported Basic RAM Macros, regarding RAM4K9, was revised to explain that it applies only to part numbers of certain revisions and earlier (SAR 29574).				
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.				
v1.5 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 6-1 • Flash-Based FPGAs.	150			
	IGLOO nano and ProASIC3 nano devices were added to Figure 6-8 • Interfacing TAP Ports and SRAM Blocks.	164			
v1.4 (October 2008)	The "SRAM/FIFO Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	150			
	The "SRAM and FIFO Architecture" section was modified to remove "IGLOO and ProASIC3E" from the description of what the memory block includes, as this statement applies to all memory blocks.	151			
	Wording in the "Clocking" section was revised to change "IGLOO and ProASIC3 devices support inversion" to "Low power flash devices support inversion." The reference to IGLOO and ProASIC3 development tools in the last paragraph of the section was changed to refer to development tools in general.	157			
	The "ESTOP and FSTOP Usage" section was updated to refer to FIFO counters in devices in general rather than only IGLOO and ProASIC3E devices.	160			
v1.3 (August 2008)	The note was removed from Figure 6-7 • RAM Block with Embedded FIFO Controller and placed in the WCLK and RCLK description.	158			
	The "WCLK and RCLK" description was revised.	159			
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 6-1 • Flash- Based FPGAs:	150			
	ProASIC3L was updated to include 1.5 V.				
	The number of PLLs for ProASIC3E was changed from five to six.				
v1.1 (March 2008)	The "Introduction" section was updated to include the IGLOO PLUS family.	147			
	The "Device Architecture" section was updated to state that 15 k gate devices do not support SRAM and FIFO.	147			
	The first note in Figure 6-1 • IGLOO and ProASIC3 Device Architecture Overview was updated to include mention of 15 k gate devices, and IGLOO PLUS was added to the second note.	149			

IGLOO and ProASIC3

For boards and cards with three levels of staging, card power supplies must have time to reach their final values before the I/Os are connected. Pay attention to the sizing of power supply decoupling capacitors on the card to ensure that the power supplies are not overloaded with capacitance.

Cards with three levels of staging should have the following sequence:

- Grounds
- Powers
- I/Os and other pins

For Level 3 and Level 4 compliance with the 30K gate device, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Cold-Sparing Support

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 μ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 7-12 on page 193). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30K gate devices do not have built-in I/O clamp diodes.

For other IGLOO and ProASIC3 devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k Ω , and the resulting current is equal to 3.3 V / 45 k Ω = 73 µA for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input LOW when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

I/O Structures in IGLOO and ProASIC3 Devices

Solution	Board Components	Speed	Current Limitations
1	Two resistors	Low to High ¹	Limited by transmitter's drive strength
2	Resistor and Zener 3.3 V	Medium	Limited by transmitter's drive strength
3	Bus switch	High	N/A
4	Minimum resistor value ^{2,3,4,5} R = 47 Ω at T _J = 70°C R = 150 Ω at T _J = 85°C R = 420 Ω at T _J = 100°C	Medium	Maximum diode current at 100% duty cycle, signal constantly at 1 52.7 mA at $T_J = 70^{\circ}$ C / 10-year lifetime 16.5 mA at $T_J = 85^{\circ}$ C / 10-year lifetime 5.9 mA at $T_J = 100^{\circ}$ C / 10-year lifetime For duty cycles other than 100%, the currents can be increased by a factor of 1 / (duty cycle). Example: 20% duty cycle at 70°C Maximum current = (1 / 0.2) × 52.7 mA = 5 × 52.7 mA = 263.5 mA

Table 7-13 • Comparison Table for 5 V–Compliant Receiver Solutions

Notes:

- 1. Speed and current consumption increase as the board resistance values decrease.
- 2. Resistor values ensure I/O diode long-term reliability.
- 3. At 70°C, customers could still use 420 Ω on every I/O.
- 4. At 85°C, a 5 V solution on every other I/O is permitted, since the resistance is lower (150 Ω) and the current is higher. Also, the designer can still use 420 Ω and use the solution on every I/O.
- 5. At 100°C, the 5 V solution on every I/O is permitted, since 420 Ω are used to limit the current to 5.9 mA.

5 V Output Tolerance

IGLOO and ProASIC3 I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, VOL = 0.4 V and VOH = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the VIL = 0.8 V and VIH = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

Schmitt Trigger

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

The Schmitt trigger is available for the LVTTL, LVCMOS, and 3.3 V PCI I/O standards.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 7-5 on page 179) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

I/O Structures in IGLOO and ProASIC3 Devices

Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

Since voltage bounce originates on the package inductance, the VMV and VCCI supplies have separate package pin assignments. For the same reason, GND and GNDQ also have separate pin assignments.

The VMV and VCCI pins must be shorted to each other on the board. Also, the GND and GNDQ pins must be shorted to each other on the board. This will prevent unwanted current draw from the power supply.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 2 and EQ 3).

Ground bounce noise voltage = L(GND) × di/dt

VCCI dip noise voltage = L(VCCI) × di/dt

EQ 3

EQ 2

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- · Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 FPGA Fabric User's Guide*.









At the system level, the skew circuit can be used in applications where transmission activities on bidirectional data lines need to be coordinated. This circuit, when selected, provides a timing margin that can prevent bus contention and subsequent data loss and/or transmitter over-stress due to transmitter-to-transmitter current shorts. Figure 8-17 presents an example of the skew circuit implementation in a bidirectional communication system. Figure 8-18 on page 238 shows how bus contention is created, and Figure 8-19 on page 238 shows how it can be avoided with the skew circuit.





Software-Controlled I/O Attributes

Users may modify these programmable I/O attributes using the I/O Attribute Editor. Modifying an I/O attribute may result in a change of state in Designer. Table 9-2 details which steps have to be re-run as a function of modified I/O attribute.

	Designer States ¹					
I/O Attribute	Compile	Layout	Fuse	Timing	Power	
Slew Control ²	No	No	Yes	Yes	Yes	
Output Drive (mA)	No	No	Yes	Yes	Yes	
Skew Control	No	No	Yes	Yes	Yes	
Resistor Pull	No	No	Yes	Yes	Yes	
Input Delay	No	No	Yes	Yes	Yes	
Schmitt Trigger	No	No	Yes	Yes	Yes	
OUT_LOAD	No	No	No	Yes	Yes	
COMBINE_REGISTER	Yes	Yes	N/A	N/A	N/A	

Table 9-2 • Designer State (resulting from I/O attribute modification)

Notes:

1. No = Remains the same, Yes = Re-run the step, N/A = Not applicable

2. Skew control does not apply to IGLOO nano, IGLOO PLUS, and ProASIC3 nano devices.

3. Programmable input delay is applicable only for ProASIC3E, ProASIC3EL, RT ProASIC3, and IGLOOe devices.



DDR for Microsemi's Low Power Flash Devices

```
DDR_OUT_0_inst : DDR_OUT
port map(DR => DataR, DF => DataF, CLK => CLK, CLR => CLR, Q => Q);
TRIBUFF_F_8U_0_inst : TRIBUFF_F_8U
port map(D => Q, E => TrienAux, PAD => PAD);
```

end DEF_ARCH;

DDR Bidirectional Buffer



Figure 10-8 • DDR Bidirectional Buffer, LOW Output Enable (HSTL Class II)

Verilog

module DDR_BiDir_HSTL_I_LowEnb(DataR,DataF,CLR,CLK,Trien,QR,QF,PAD);

```
input DataR, DataF, CLR, CLK, Trien;
output QR, QF;
inout PAD;
wire TrienAux, D, Q;
INV Inv_Tri(.A(Trien), .Y(TrienAux));
DDR_OUT DDR_OUT_0_inst(.DR(DataR),.DF(DataF),.CLK(CLK),.CLR(CLR),.Q(Q));
DDR_REG DDR_REG_0_inst(.D(D),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));
BIBUF_HSTL_I BIBUF_HSTL_I_0_inst(.PAD(PAD),.D(Q),.E(TrienAux),.Y(D));
```

endmodule



Security in Low Power Flash Devices



Figure 12-3 • Block Representation of the AES Decryption Core in a Fusion AFS600 FPGA

Security Features

IGLOO and ProASIC3 devices have two entities inside: FlashROM and the FPGA core fabric. Fusion devices contain three entities: FlashROM, FBs, and the FPGA core fabric. The parts can be programmed or updated independently with a STAPL programming file. The programming files can be AES-encrypted or plaintext. This allows maximum flexibility in providing security to the entire device. Refer to the "Programming Flash Devices" section on page 287 for information on the FlashROM structure.

Unlike SRAM-based FPGA devices, which require a separate boot PROM to store programming data, low power flash devices are nonvolatile, and the secured configuration data is stored in on-chip flash cells that are part of the FPGA fabric. Once programmed, this data is an inherent part of the FPGA array and does not need to be loaded at system power-up. SRAM-based FPGAs load the configuration bitstream upon power-up; therefore, the configuration is exposed and can be read easily.

The built-in FPGA core, FBs, and FlashROM support programming files encrypted with the 128-bit AES (FIPS-192) block ciphers. The AES key is stored in dedicated, on-chip flash memory and can be programmed before the device is shipped to other parties (allowing secure remote field updates).

Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash devices and the $\text{ARM}^{\$}$ -enabled flash devices, which have the M1 and M7 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design is encrypted along with the ARM IP, according to the details below.



Note: The settings in this figure are used to show the generation of an AES-encrypted programming file for the FPGA array, FlashROM, and FB contents. One or all locations may be selected for encryption.

Figure 12-17 • Settings to Program a Device Secured with FlashLock and using AES Encryption

Choose the **High** security level to reprogram devices using both the FlashLock Pass Key and AES key protection (Figure 12-18 on page 321). Enter the AES key and click **Next**.

A device that has already been secured with FlashLock and has an AES key loaded must recognize the AES key to program the device and generate a valid bitstream in authentication. The FlashLock Key is only required to unlock the device and change the security settings.

This is what makes it possible to program in an untrusted environment. The AES key is protected inside the device by the FlashLock Key, so you can only program if you have the correct AES key. In fact, the AES key is not in the programming file either. It is the key used to encrypt the data in the file. The same key previously programmed with the FlashLock Key matches to decrypt the file.

An AES-encrypted file programmed to a device without FlashLock would not be secure, since without FlashLock to protect the AES key, someone could simply reprogram the AES key first, then program with any AES key desired or no AES key at all. This option is therefore not available in the software.

Security in ARM-Enabled Low Power Flash Devices

There are slight differences between the regular flash device and the ARM-enabled flash devices, which have the M1 prefix.

The AES key is used by Microsemi and preprogrammed into the device to protect the ARM IP. As a result, the design will be encrypted along with the ARM IP, according to the details below.

Cortex-M1 and Cortex-M3 Device Security

Cortex-M1–enabled and Cortex-M3 devices are shipped with the following security features:

- FPGA array enabled for AES-encrypted programming and verification
- · FlashROM enabled for AES-encrypted write and verify
- Embedded Flash Memory enabled for AES encrypted write



Figure 13-1 • AES-128 Security Features

Microprocessor Programming of Microsemi's Low Power Flash Devices

Microprocessor Programming Support in Flash Devices

The flash-based FPGAs listed in Table 15-1 support programming with a microprocessor and the functions described in this document.

Table 15-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 15-1. Where the information applies to only one device or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 15-1. Where the information applies to only one device or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

UJTAG Applications in Microsemi's Low Power Flash Devices

Silicon Testing and Debugging

In many applications, the design needs to be tested, debugged, and verified on real silicon or in the final embedded application. To debug and test the functionality of designs, users may need to monitor some internal logic (or nets) during device operation. The approach of adding design test pins to monitor the critical internal signals has many disadvantages, such as limiting the number of user I/Os. Furthermore, adding external I/Os for test purposes may require additional or dedicated board area for testing and debugging.

The UJTAG tiles of low power flash devices offer a flexible and cost-effective solution for silicon test and debug applications. In this solution, the signals under test are shifted out to the TDO pin of the TAP Controller. The main advantage is that all the test signals are monitored from the TDO pin; no pins or additional board-level resources are required. Figure 17-6 illustrates this technique. Multiple test nets are brought into an internal MUX architecture. The selection of the MUX is done using the contents of the TAP Controller instruction register, where individual instructions (values from 16 to 127) correspond to different signals under test. The selected test signal can be synchronized with the rising or falling edge of TCK (optional) and sent out to UTDO to drive the TDO output of JTAG.

For flash devices, TDO (the output) is configured as low slew and the highest drive strength available in the technology and/or device. Here are some examples:

- 1. If the device is A3P1000 and VCCI is 3.3 V, TDO will be configured as LVTTL 3.3 V output, 24 mA, low slew.
- If the device is AGLN020 and VCCI is 1.8 V, TDO will be configured as LVCMOS 1.8 V output, 4 mA, low slew.
- 3. If the device is AGLE300 and VCCI is 2.5 V, TDO will be configured as LVCMOS 2.5 V output, 24 mA, low slew.

The test and debug procedure is not limited to the example in Figure 17-5 on page 369. Users can customize the debug and test interface to make it appropriate for their applications. For example, multiple test signals can be registered and then sent out through UTDO, each at a different edge of TCK. In other words, *n* signals are sampled with an F_{TCK} / *n* sampling rate. The bandwidth of the information sent out to TDO is always proportional to the frequency of TCK.



Figure 17-6 • UJTAG Usage Example in Test and Debug Applications



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